

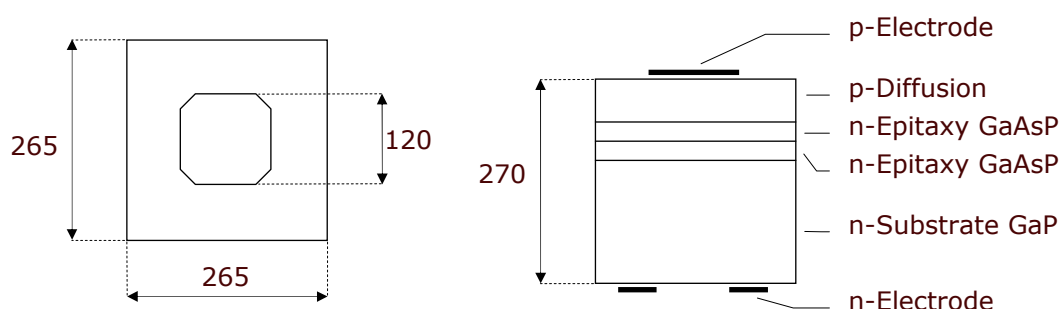
**TSN-RED**

**Item No.: 192220**

1. This specification applies to GaAsP / GaP LED Chips
2. Structure
  - 2.1 Mesa structure
  - 2.2 Electrodes
 

p-side (anode)	Au alloy
n-side (cathode)	Au alloy

3. Outlines (dimensions in microns)



Wire bond contacts can also be circular or square

4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	$V_F$	$I_F = 20 \text{ mA}$		2,05	2,50	V
Reverse current	$I_R$	$V_R = 5 \text{ V}$			10	$\mu\text{A}$
Luminous intensity *	$I_V$	$I_F = 20 \text{ mA}$	3,0	4,0		mcd
Peak wavelength	$\lambda_P$	$I_F = 20 \text{ mA}$		650		nm

\* On request, wafers will be delivered according to luminous intensity classes  
Brightness measurement at OSA on gold plate

5. Packing

- 1) wire bond side on top
- 2) back contact on top

6. Labeling

Type	Lot No.	I <sub>v</sub> typ	Quantity
		min	
		max	